

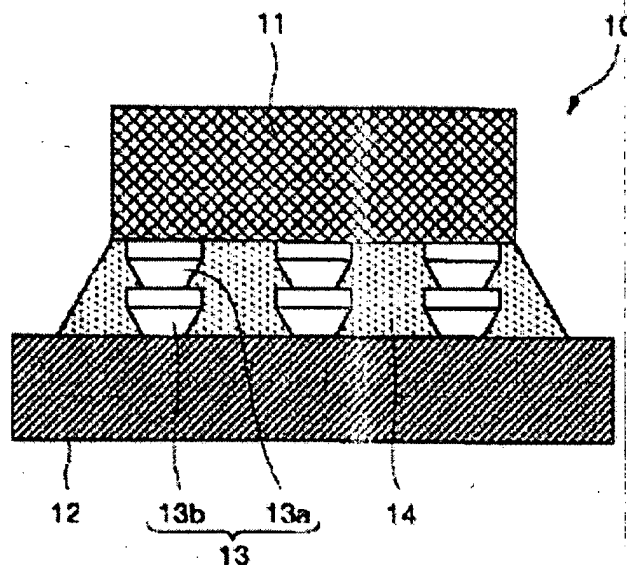
SEMICONDUCTOR SENSOR AND FABRICATION THEREOF

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Abstract of JP2000243783

PROBLEM TO BE SOLVED: To provide a semiconductor sensor comprising a semiconductor sensor, in which stress and flexure hindering miniaturization of semiconductor sensor can be reduced. **SOLUTION:** When a semiconductor sensor chip 11 is a bare chip mounted on a substrate 12, a metal pole 13 for conducting an electrode on the rear surface of the sensor chip with a wiring pattern on the substrate is provided. The metal pole is formed by stacking a first metal protrusion 13a on a second metal protrusion 13b. A plurality of metal poles are arranged adjacently, and the gap between the metal poles is filled with a bonding material. Since a significantly high metal pole can be formed as compared with a conventional one, transmission of stress and flexure is suppressed, and the semiconductor sensor can sustain high measurement accuracy. Consequently, the semiconductor sensor can be miniaturized.



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